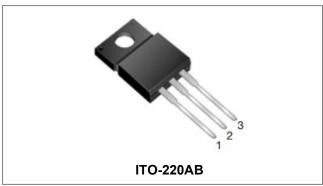




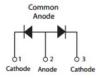
MBRF10100CTR SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- **Reverse battery protection**

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V_{RRM}	-		
Working Peak Reverse Voltage	V_{RWM}		100	V
DC Blocking Voltage	V_R			
Average Destified Femiliand Comment		50% duty cycle @Tc=105°C, rectangular	5(Per Leg)	
Average Rectified Forward Current	IF (AV)	wave form	10(Per Device)	А
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	120	Α

Electrical Characteristics:

Characteristics	Symbol	Ol Condition		Max.	Units
Forward Voltage Drop(Per Leg)*	V _{F1}	@5A, Pulse, T _J = 25 °C	0.79	0.85	V
	V _{F2}	@5A, Pulse, T _J = 125 °C	0.65	0.75	V
Reverse Current(Per Leg)*	verse Current(Per Leg)* I_{R1} @V _R = rated V _R , T _J = 25 °C		0.02	1.0	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	4	15	mA
Junction Capacitance(Per Leg)	Ст	C_T @V _R = 5V, T_C = 25 °C, f_{SIG} = 1MHz		300	pF
Series Inductance(Per Leg)	Ls	_s Measured lead to lead 5 mm from package body		-	nH
Voltage Rate of Change	dv/dt	-		10,000	V/μs
RSM Isolation Voltage (t = 1.0 second, R. H. < =30%, T _A = 25 °C)	V _{ISO}	Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	-	4500	V
·		Clip mounting, the epoxy body is inside the heatsink.	-	3500	
		Screw mounting, the epoxy body is inside the heatsink.	-	1500	

Pulse width < 300 µs, duty cycle < 2%

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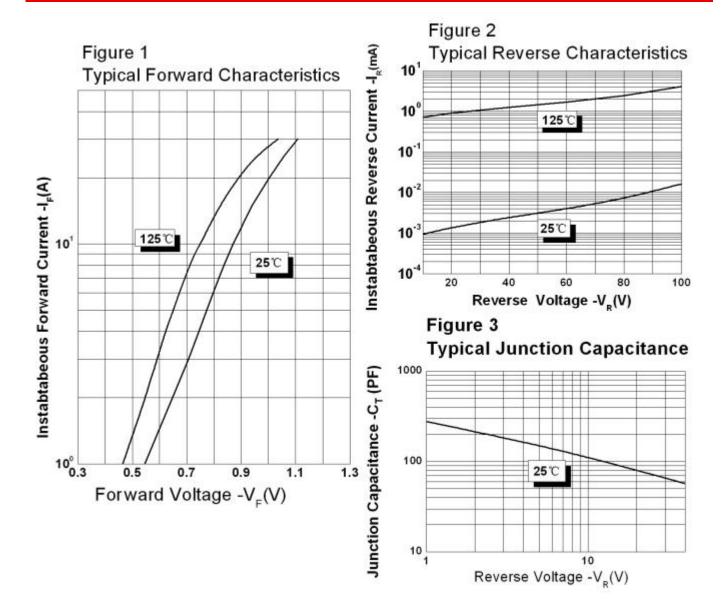




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	4.5	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

Ratings and Characteristics Curves



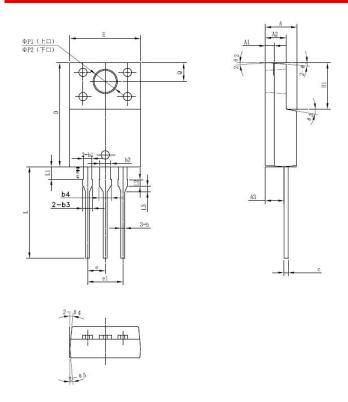
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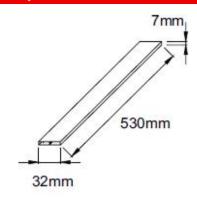


Mechanical Dimensions ITO-220AB



SYMBOL	Millimeters				
STWIBUL	MIN.	TYP.	MAX.		
Α	4.30	4.50	4.70		
A1	1.10	1.30	1.50		
A2	2.80	3.00	3.20		
A3	2.50	2.70	2.90		
b	0.50	0.60	0.75		
b1	1.10	1.20	1.35		
b2	1.50	1.60	1.75		
b3	1.20	1.30	1.45		
b4	1.60	1.70	1.85		
С	0.50	0.60	0.75		
D	14.80	15.00	15.20		
E	9.96	10.16	10.36		
е		2.55			
e1		5.10			
H1	6.50	6.70	6.90		
L	12.70	13.20	13.70		
L1	1.60	1.80	2.00		
L2	0.80	1.00	1.20		
L3	0.60	0.80	1.00		
ФР1(上□)	3.30	3.50	3.70		
ΦP2 (下口)	2.99	3.19	3.39		
Q	2.50	2.70	2.90		
Θ1		5°			
Θ2		4°			
Θ3		10°			
Θ4		5°			
Θ5		5°			

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

 MBR
 = Device Type

 F
 = Package type

 10
 = Forward Current (10A)

 100
 = Reverse Voltage (100V)

 CTR
 = Configuration

 SSG
 = SSG

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
MBRF10100CTR	ITO-220AB (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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